

國立臺灣師範大學 104 學年度碩士班招生考試試題

科目：電子學

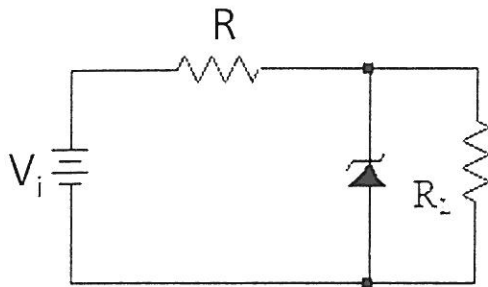
適用系所：光電科技研究所

注意：1.本試題共 3 頁，請依序在答案卷上作答，並標明題號，不必抄題。2.答案必須寫在指定作答區內，否則不予計分。

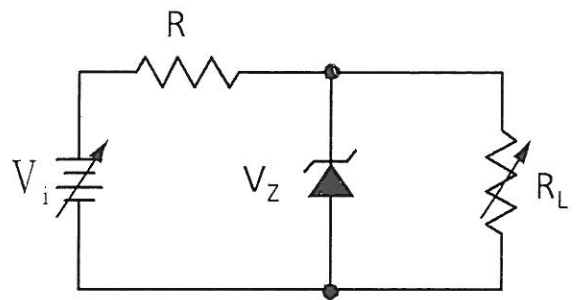
第 1-4 題，必需運算過程 第 5-9 題 選擇題，無需計算過程

1. The circuit including a Zener diode is shown as the following figure. (A) Please find the minimum R_L while the Zener diode is operated in the breakdown region. Here, $R = 0.5k \Omega$, $r_z = 20 \Omega$, $I_{zk} = 2mA$, $V_z = 6.7 V$. (7 分) (B) Please find the maximum power consumption of the Zener diode, operated in the breakdown region. (8 分) Here, $R = 100 \Omega$, (the breakdown voltage of the Zener diode) $V_z = 10V$, $12 V \leq V_i \leq 15 V$, $500 \Omega \leq R_L \leq 1000 \Omega$.

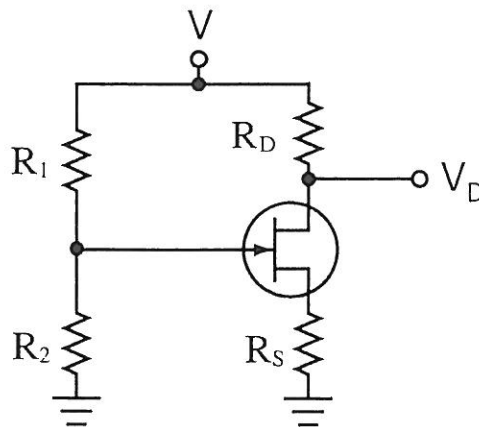
(A)



(B)

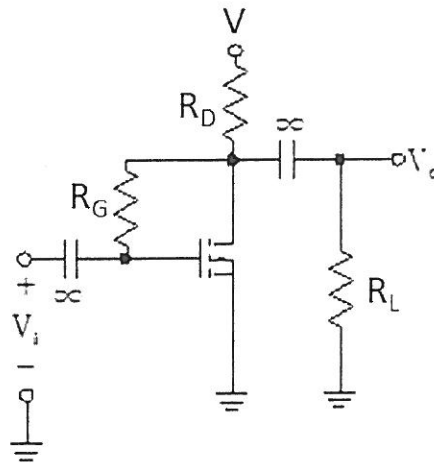


2. The circuit including a FET is shown as the following figure. Please find the R_S . Here, $V = 15V$, $V_{GS} = -2V$, $V_D = 12V$, $R_1 = 90k\Omega$, $R_2 = 45 k\Omega$, $R_D = 1.5 k\Omega$ (15 分)

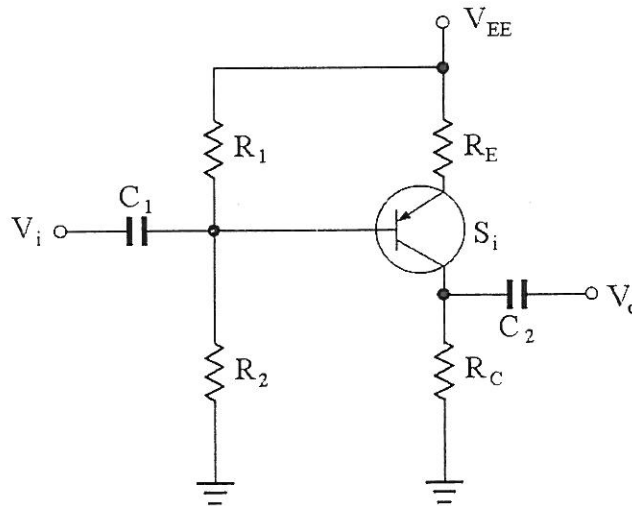


國立臺灣師範大學 104 學年度碩士班招生考試試題

3. The circuit including an N-channel MOSFET is shown as the following figure. Please find the voltage gain V_o/V_i of small signal analysis. Here, in the operation point of the MOSFET, $I_D = 0.6 \text{ mA}$, (threshold voltage) $V_T = 1 \text{ V}$. $V = 5 \text{ V}$, $R_D = 5 \text{ k}\Omega$, $R_L = 10 \text{ k}\Omega$, $R_G = 10 \text{ M}\Omega$. (15 分)



4. The circuit including a transistor is shown as the following figure. Please find V_{CE} . Here, $V_{EE} = 10 \text{ V}$, $R_1 = 10 \text{ k}\Omega$, $R_2 = 40 \text{ k}\Omega$, $R_E = 2 \text{ k}\Omega$, $R_C = 1.5 \text{ k}\Omega$. (15 分)



5. The characteristics of the diode exclude which one? (A) The effect of diffusion capacitance happens while the reverse bias is applied (B) The reverse current increases while the temperature rise (C) The cut-in voltage decreases while the temperature rise (D) The depletion capacitance decreases while the reverse bias increases (8 分)

國立臺灣師範大學 104 學年度碩士班招生考試試題

6. The characteristics of the field effect transistor (FET) exclude which one?
(A)Low thermal stability (B)Low noise (C)High input impedance (D)The transportation of uni-polar carrier(8 分)
7. To fabricate the p-type semiconductor, which element could be doped into the intrinsic semiconductor? (A)Boron (B) phosphorous (C)Arsenic (D)Antimony(8 分)
8. To turn on a enhancement-mode p-channel MOSFET, the applied gate voltage is which one? (A) Negative voltage (B)Positive voltage (C) Both positive and negative voltage (D) Zero voltage(8 分)
9. The advantages of transformer-coupled amplifier exclude which one? (A) Improvement of frequency response (B)Impedance matching between former and later components (C)DC isolation effect (D) Promotion of Power transfer efficiency (8 分)

